SILICON POWER RECTIFIER- SWITCHING

DESCRIPTION:

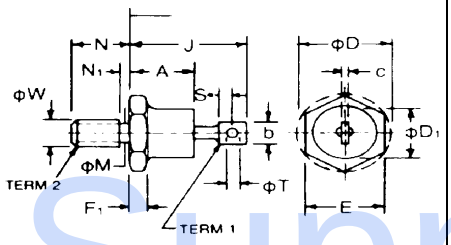
The **1N3883/R** is Designed for General Purpose Fast Switching Power Supply Applications.

- **1N3883** = Cathode to Stud
- **1N3883R** = Anode to Stud

MAXIMUM RATINGS

I_O	6.0 A @ T_C = 100 ^{O}C
I_{FSM}	150 A (ONE CYCLE)
V_{RWM}	V_R = 400 V
T_J	-65 ^{O}C to +150 ^{O}C
T_{STG}	-65 ^{O}C to +175 ^{O}C
θ_{JC}	3.0 ^{O}C/W

PACKAGE STYLE DO- 4



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A		0.405		10.28
b		0.250		6.35
c				
ΦD		0.505		12.82
ΦD1	0.265	0.424	6.74	10.76
E	0.423	0.438	10.75	11.12
F1	0.075	0.175	1.91	4.44
J	0.600	0.800	15.24	20.32
ΦM	0.163	0.189	4.15	4.80
N	0.422	0.453	10.72	11.50
N1		0.078		1.98
S				
ΦT	0.060	0.095	1.53	2.41
ΦW	10-32	UNF-2A	10-32	UNF-2A

CHARACTERISTICS T_J = 25 ^{O}C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
I_R	V_R = 400 V			10	15	µA
		T_C = 100 ^{O}C		0.5	1.0	mA
V_F	I_F = 6.0 A			1.0	1.4	V
	I_F = 19 A	T_C = 150 ^{O}C		1.2	1.5	
t_{rr}	I_F = 1.0 A	$V_R \geq$ 30 V			200	nS
$I_{RM(REC)}$	I_F = 1.0 A	$V_R \geq$ 30 V			2.0	A